

GL4100

Side View and Thin Flat Type Infrared Emitting Diode

■ Features

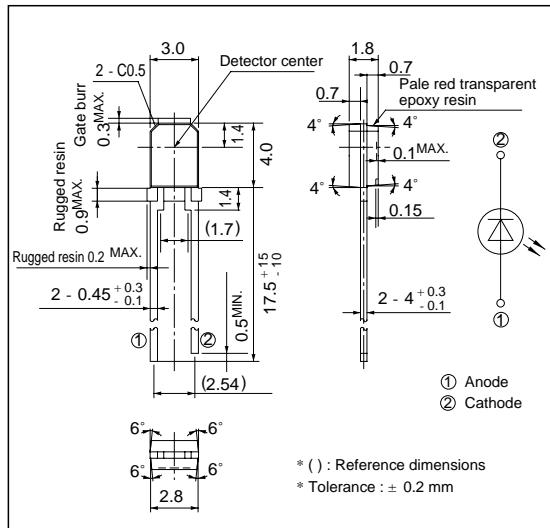
1. Compact flat package
2. Wide beam angle
(Half intensity angle : $\pm 90^\circ$)

■ Applications

1. Mouses
2. Track balls

■ Outline Dimensions

(Unit : mm)



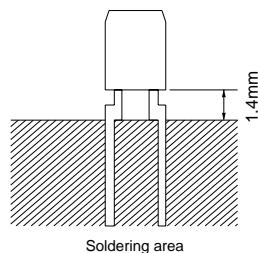
■ Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Forward current	I _F	50	mA
* ¹ Peak forward current	I _{FM}	1	A
Reverse voltage	V _R	6	V
Power dissipation	P	75	mW
Operating temperature	T _{opr}	- 25 to + 85	°C
Storage temperature	T _{stg}	- 40 to + 85	°C
* ² Soldering temperature	T _{sol}	260	°C

* 1 Pulse width $\leq 100\mu s$, Duty ratio=0.01

* 2 For 5 seconds at the position of 1.4 mm from the resin edge



■ Electro-optical Characteristics

(Ta=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage	V _F	I _F = 20mA	-	1.2	1.4	V
Peak forward voltage	V _{FM}	I _{FM} = 0.5A	-	3.0	4.0	V
Reverse current	I _R	V _R = 3V	-	-	10	μA
Radiant flux	Φ _e	I _F = 20mA	1.0	-	2.0	mW
Peak emission wavelength	λ _p	I _F = 5mA	-	950	-	nm
Half intensity wavelength	Δλ	I _F = 5mA	-	45	-	nm
Terminal capacitance	C _t	V _R = 0, f = 1MHz	-	50	-	pF
Response frequency	f _c		-	300	-	kHz
Half intensity angle	Δθ	I _F = 20mA	-	± 90	-	°

Fig. 1 Forward Current vs. Ambient Temperature

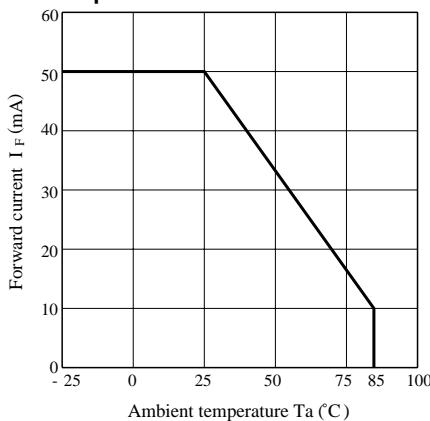


Fig. 2 Peak Forward Current vs. Duty Ratio

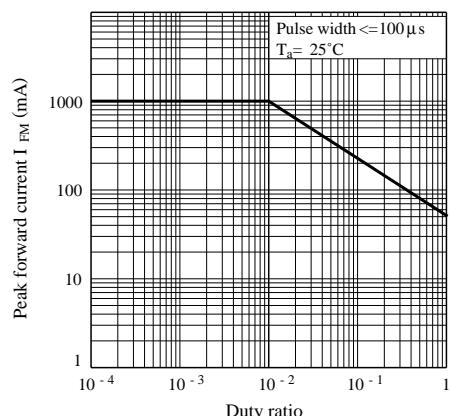
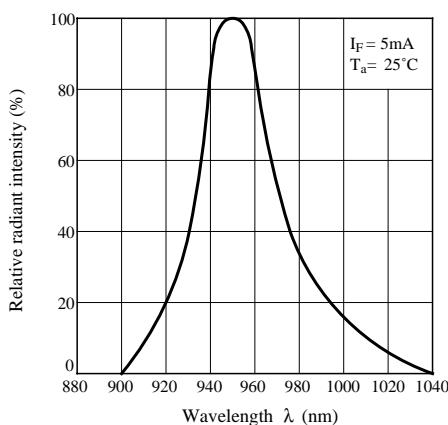
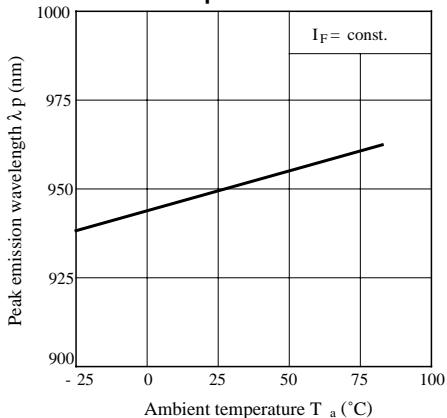
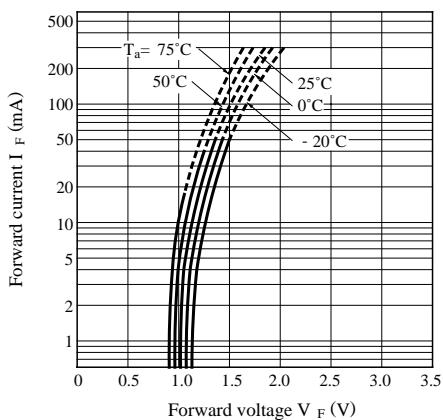
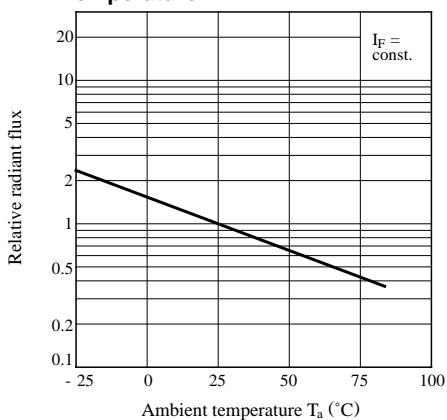
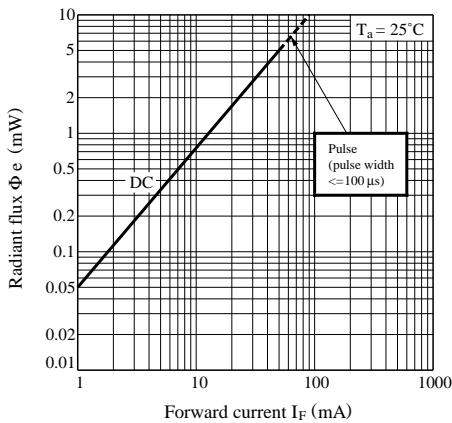
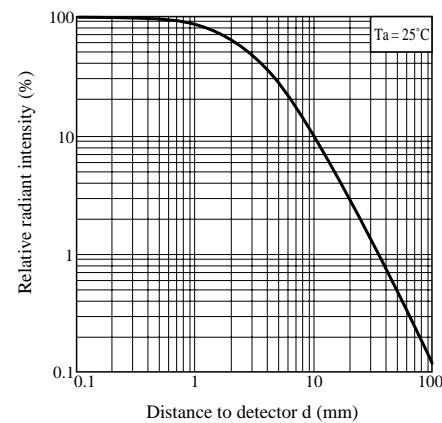


Fig. 3 Spectral Distribution**Fig. 4 Peak Emission Wavelength vs. Ambient Temperature****Fig. 5 Forward Current vs. Forward Voltage****Fig. 6 Relative Radiant Flux vs. Ambient Temperature****Fig. 7 Radiant Flux vs. Forward Current****Fig. 8 Relative Radiant Intensity vs. Distance**

**Fig. 9 Relative Radiant Intensity vs.
Distance (Detector : PT4110)**

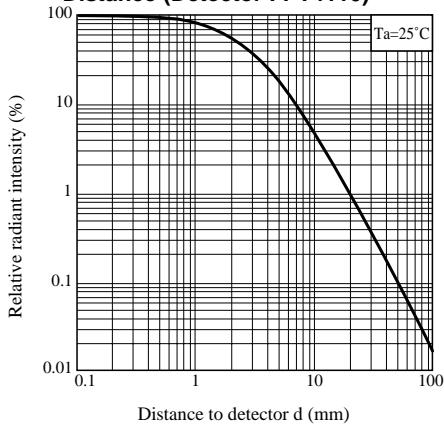
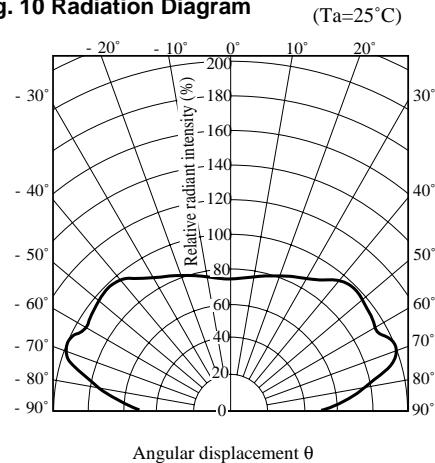


Fig. 10 Radiation Diagram



- Please refer to the chapter "Precautions for Use". (Page 78 to 93)